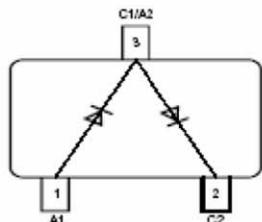


FEATURES

- For high-speed switching applications
- Connected in series


MARKING: A7
Maximum Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Limits	Unit
Reverse voltage	V_R	75	V
Forward current	I_F	150	mA
Forward power dissipation	P_D	200	mW
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 100\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R = 75\text{V}$ $V_R = 20\text{V}$		2.5 25	μA nA
Forward voltage	V_F	$I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0\text{V}$ $f = 1\text{MHz}$		2	pF
Reveres recovery time	t_{rr}	$I_F = I_R = 10\text{mA}$ $I_{rr} = 0.1 \times I_R$ $R_L = 100\Omega$		4	nS

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